

深圳市晶泰源电子有限公司

SS8550LT1 TRANSISTOR(PNP)

FEATURES

MARKING: Y2

Power dissipation

P_{CM} : 0.3 W ($T_{amb}=25^{\circ}C$)

Collector current

I_{CM} : -1.5 A

Collector-base voltage

$V_{(BR)CBO}$: -40 V

Operating and storage junction temperature range

T_J, T_{stg} : $-55^{\circ}C$ to $+150^{\circ}C$

ELECTRICAL CHARACTERISTICS ($T_{amb}=25^{\circ}C$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=-100\mu A, I_E=0$	-40			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=-100\mu A, I_B=0$	-25			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=-100\mu A, I_C=0$	-5			V
Collector cut-off current	I_{CBO}	$V_{CB}=-30V, I_E=0$			-0.1	μA
Collector cut-off current	I_{CEO}	$V_{CE}=-20V, I_B=0$			-0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=-5V, I_C=0$			-0.1	μA
DC current gain	$h_{FE(1)}$	$V_{CE}=-1V, I_C=-100mA$	120		350	
	$h_{FE(2)}$	$V_{CE}=-1V, I_C=-800mA$	40			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=-800mA, I_B=-80mA$			-0.5	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C=-800mA, I_B=-80mA$			-1.2	V
Transition frequency	f_T	$V_{CE}=-10V, I_E=-50mA$ $f=30MHz$	100			MHz

CLASSIFICATION OF $h_{FE(1)}$

Rank				
Range	120~200	200~350		

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